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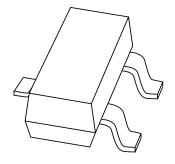
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BAS116 Low-leakage diode

Product data sheet Supersedes data of 1999 May 26 2003 Dec 12



Low-leakage diode

BAS116

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

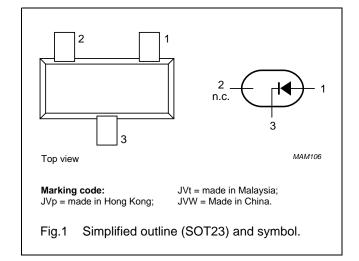
Low leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial medium-speed switching diode with a low leakage current in a small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
TIPE NOWIBER	NAME	DESCRIPTION	VERSION
BAS116	_	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		_	85	V
V _R	continuous reverse voltage		_	75	V
I _F	continuous forward current	see Fig.2; note 1	_	215	mA
I _{FRM}	repetitive peak forward current		_	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		$t_p = 1 \mu s$	_	4	Α
		$t_p = 1 \text{ ms}$	_	1	Α
		t _p = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

Low-leakage diode

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ELECTRICAL CHARACTERISTICS

 T_i = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS		MAX.	UNIT
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	_	0.9	V
		I _F = 10 mA	_	1	V
		I _F = 50 mA	_	1.1	V
		I _F = 150 mA	_	1.25	V
I _R	reverse current	see Fig.5			
		V _R = 75 V	0.003	5	nA
		V _R = 75 V; T _j = 150 °C	3	80	nA
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	2	_	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	0.8	3	μS

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-tp)}	thermal resistance from junction to tie-point		330	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

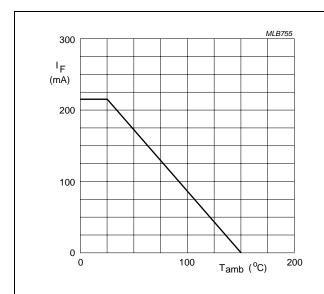
Note

1. Device mounted on an FR4 printed-circuit board.

Low-leakage diode

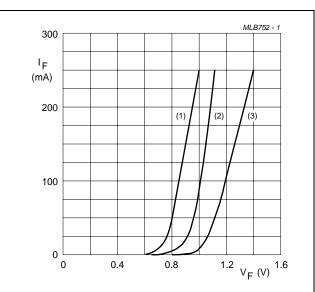
BAS116

GRAPHICAL DATA



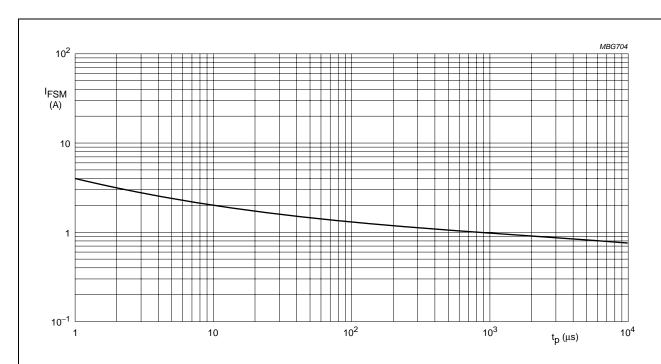
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



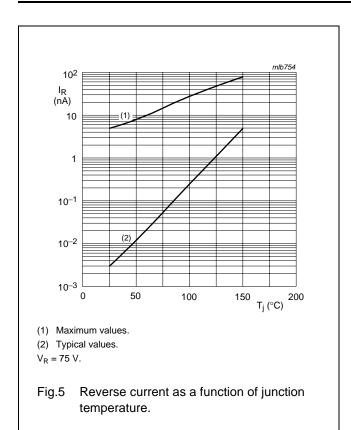
Based on square wave currents; $T_j = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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Low-leakage diode

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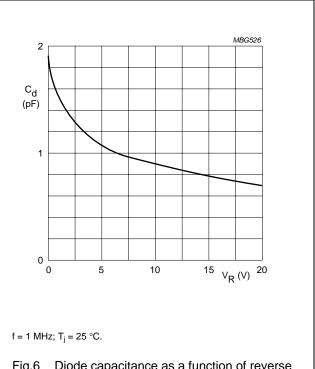
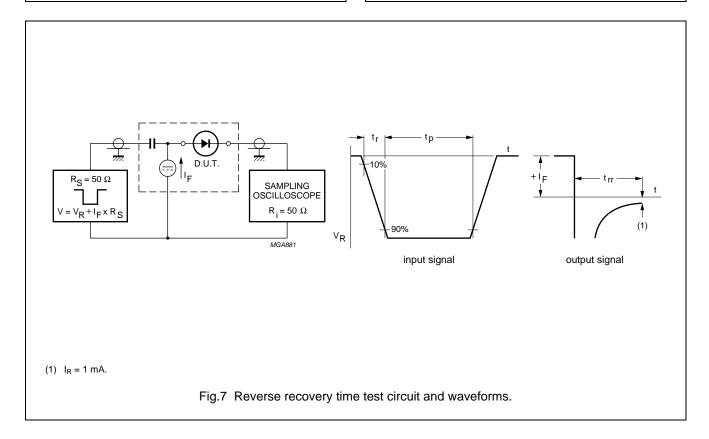


Fig.6 Diode capacitance as a function of reverse voltage; typical values.



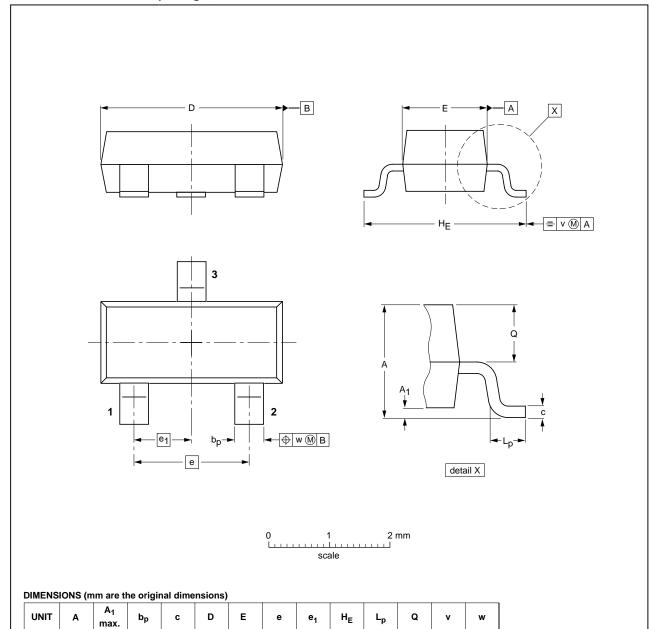
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04 06-03-16

0.95

2.5

2.1

0.45

0.15

0.55

0.2

0.1

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0.15

0.09

0.1

mm

3.0

2.8

1.4

1.2

Low-leakage diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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